What is claimed is:

1. A resist composition generating an acid upon exposure and having solubility in a developing solution, which is changed by action of an acid, the resist composition comprising:

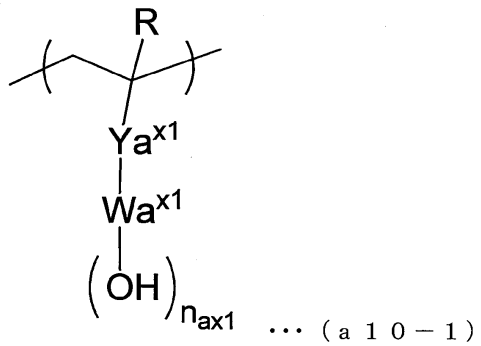
a resin component (A1) that has a constitutional unit (a1) containing an acid-decomposable group having a polarity which is increased by action of an acid and a constitutional unit (a10) represented by General Formula (a10-1); and

a plasticizer component (Z) that has a constitutional unit (z1) represented by General Formula (z1-1) and does not contain an acid-dissociable group,

wherein a content of the plasticizer component (Z) is 50 parts by mass or less with respect to 100 parts by mass of the resin component (A1),

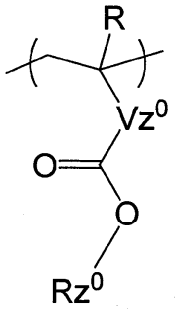
wherein a weight-average molecular weight (Mw), based on a polystyrene-equivalent value determined by gel permeation chromatography (GPC), of the component (Z) is in a range of 5,000 to 200,000, and

a solid content concentration is 25% by mass or more,



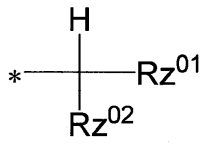
... (a10-1)

wherein R represents a hydrogen atom, an alkyl group having 1 to 5 carbon atoms, or a halogenated alkyl group having 1 to 5 carbon atoms, Ya^{x1} represents a single bond or a divalent linking group, Wa^{x1} represents an aromatic hydrocarbon group which may have a substituent, and n_{ax1} represents an integer of 1 or greater;



・・・（ｚ１－１）

wherein R represents a hydrogen atom, an alkyl group having 1 to 5 carbon atoms, or a halogenated alkyl group having 1 to 5 carbon atoms, Vz^0 represents a single bond or a divalent hydrocarbon group which may contain a hetero atom, provided that in a case where Vz^0 represents a divalent hydrocarbon group which may contain a hetero atom, Vz^0 does not contain an acid-dissociable group, and Rz^0 represents a hydrogen atom or a group represented by General Formula (z1-r-1):

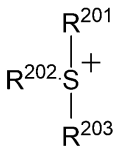


・・・（ｚ１－ｒ－１）

wherein Rz^{01} represents a hydrocarbon group which may have a substituent, Rz^{02} represents a hydrogen atom or a hydrocarbon group which may have a substituent, Rz^{01} and Rz^{02} may be bonded to each other to form a ring structure, provided that Rz^{01} and Rz^{02} do not contain an acid-dissociable group, and * represents a bond.

2. The resist composition according to Claim 1, further comprising an acid generator component (B),

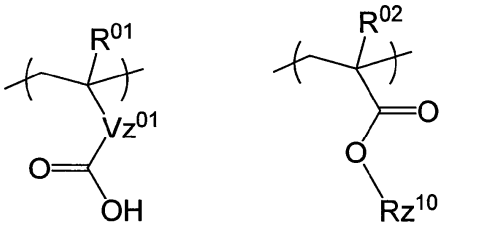
wherein a cation moiety of the acid generator component (B) is a cation represented by general formula (ca-1) shown below:



・・・(ca－1)

wherein R^{201} is an aryl group which may have a substituent; R^{202} and $R^{203}$are bonded to each other to form a ring together with the sulfur atom in the formula.

3. The resist composition according to Claim 1 or 2, wherein the plasticizer component (Z) comprises a constitutional unit (z1-1-1) represented by general formula (z1-1-1) shown below and a constitutional unit (z1-1-2) represented by general formula (z1-1-2) shown below:



(z 1 − 1 − 1) (z 1 − 1 − 2)

wherein R^{01} and R^{02} each independently represent a hydrogen atom, an alkyl group having 1 to 5 carbon atoms, or a halogenated alkyl group having 1 to 5 carbon atoms; Vz^{01} represents a single bond, -C(=O)-O-Y^{21}- or -C(=O)-O-Y^{21}-O-C(=O)-Y^{22}-; Y^{21} and Y^{22} each independently represent a divalent hydrocarbon group which may have a substituent, and O represents an oxygen atom; and when Vz^{01} represents -C(=O)-O-Y^{21}- or -C(=O)-O-Y^{21}-O-C(=O)-Y^{22}-, Vz^{01} does not contain an acid-dissociable group; Rz^{10} represents a linear alkyl group, -Rz^{11}-O-Rz^{12}, or a monovalent alicyclic hydrocarbon group; Rz^{11} represents a linear alkylene group, and Rz^{12} represents a linear alkyl group.

4. The resist composition according to any one of Claims 1 to 3, wherein the content of the plasticizer component (Z) is 1 to 30 parts by mass with respect to 100 parts by mass of the resin component (A1).

5. A method of forming a resist pattern, comprising:

a step of forming a resist film on a support using the resist composition according to any one of Claims 1 to 4;

a step of exposing the resist film; and

a step of developing the exposed resist film to form a resist pattern.